onsemi

Amplifier Transistors

NPN Silicon

BC546B, BC547A, B, C, BC548B, C

Features

• Pb-Free Packages are Available*

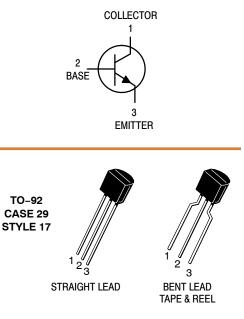
MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Collector - Emitter Voltage	BC546 BC547 BC548	V _{CEO}	65 45 30	Vdc
Collector - Base Voltage	BC546 BC547 BC548	V _{CBO}	80 50 30	Vdc
Emitter - Base Voltage		V _{EBO}	6.0	Vdc
Collector Current – Continuous		Ι _C	100	mAdc
Total Device Dissipation @ $T_A = 2$ Derate above 25°C	5°C	PD	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 2$ Derate above 25°C	25°C	PD	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range		T _J , T _{stg}	–55 to +150	°C

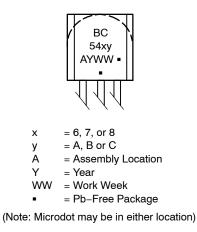
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

*For additional information on our Pb–Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

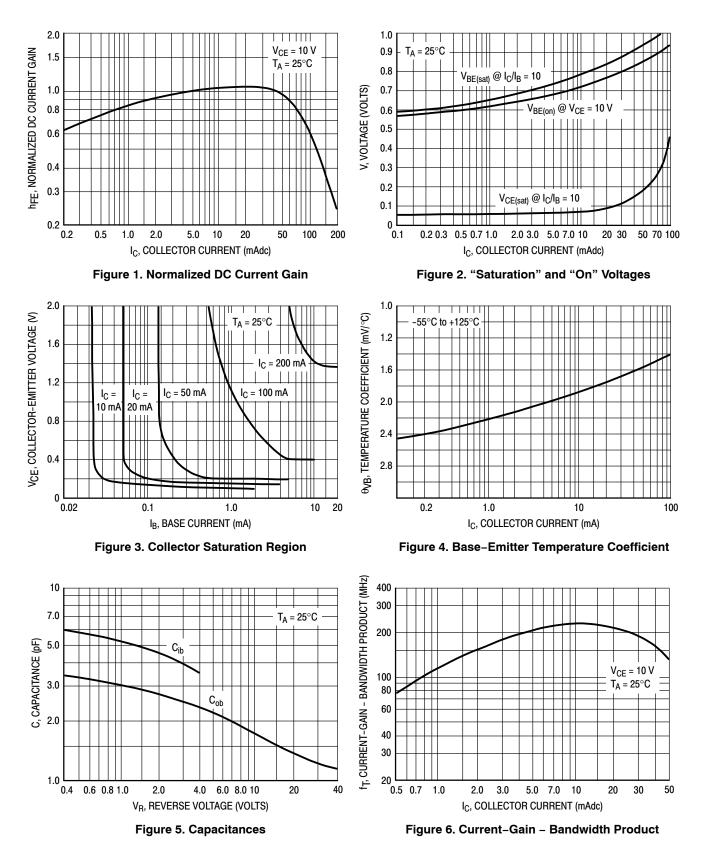
BC546B, BC547A, B, C, BC548B, C

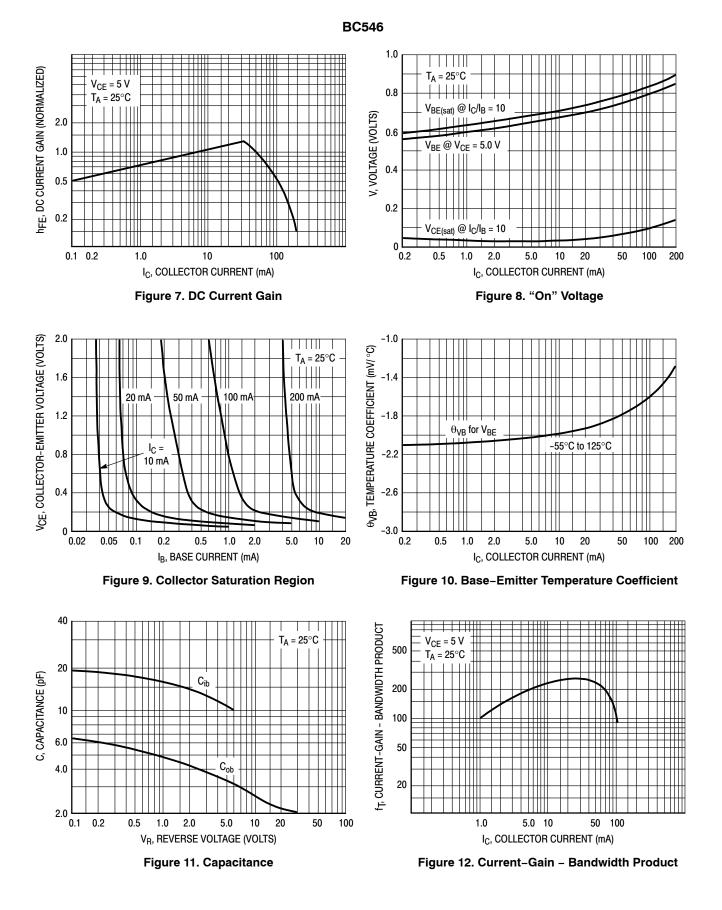
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•	•	•	•	
Collector – Emitter Breakdown Voltage	Variation	1	İ	1	V
$(I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0)$ BC546	V _{(BR)CEO}	65	_	_	v
(iC = 1.0 m/z, iB = 0) BC547		45	_	_	
BC548		30		_	
D0348			_	_	
Collector – Base Breakdown Voltage	V _{(BR)CBO}				V
$(I_{\rm C} = 100 \mu {\rm Adc})$ BC546	()	80	-	-	
BC547		50	-	-	
BC548		30	-	-	
			-		
Emitter – Base Breakdown Voltage	V _{(BR)EBO}				V
$(I_{\rm E} = 10 \ \mu {\rm A}, \ I_{\rm C} = 0)$ BC546		6.0	-	-	
BC547		6.0	-	-	
BC548		6.0	-	-	
Collector Cutoff Current	I _{CES}				
$(V_{CE} = 70 \text{ V}, V_{BE} = 0)$ BC546	ICES		0.2	15	nA
		_			IIA
$(V_{CE} = 50 \text{ V}, V_{BE} = 0)$ BC547		-	0.2	15	
$(V_{CE} = 35 V, V_{BE} = 0)$ BC548		-	0.2	15	
$(V_{CE} = 30 \text{ V}, \text{ T}_{A} = 125^{\circ}\text{C})$ BC546/547/548		-	-	4.0	μA
ON CHARACTERISTICS					
DC Current Gain	h				1
	h _{FE}				-
$(I_{C} = 10 \ \mu A, V_{CE} = 5.0 \ V)$ BC547A		-	90	-	
BC546B/547B/548B		-	150	-	
BC548C		-	270	-	
$(I_{\rm C} = 2.0 \text{ mA}, V_{\rm CE} = 5.0 \text{ V})$ BC546		110	-	450	
BC547		110	-	800	
BC548		110	-	800	
BC547A		110	180	220	
BC546B/547B/548B		200	290	450	
BC547C/BC548C		420	520	800	
(I _C = 100 mA, V _{CE} = 5.0 V) BC547A/548A		_	120	_	
BC546B/547B/548B		_	180		
BC548C		_	300	_	
				-	
Collector – Emitter Saturation Voltage	V _{CE(sat)}				V
(I _C = 10 mA, I _B = 0.5 mA)		-	0.09	0.25	
(I _C = 100 mA, I _B = 5.0 mA)		-	0.2	0.6	
$(I_C = 10 \text{ mA}, I_B = \text{See Note 1})$		-	0.3	0.6	
	. V		0.7		V
Base – Emitter Saturation Voltage	V _{BE(sat)}	-	0.7	-	v
(l _C = 10 mA, l _B = 0.5 mA)					
Base – Emitter On Voltage	V _{BE(on)}				V
$(I_{C} = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V})$	DE(01)	0.55	_	0.7	
(I _C = 2.0 mA, V _{CE} = 5.0 V) (I _C = 10 mA, V _{CE} = 5.0 V)		_	_	0.77	
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product	f _T				MHz
(I _C = 10 mA, V _{CE} = 5.0 V, f = 100 MHz) BC546	'	150	300	_	
BC547		150	300	_	
BC548		150	300	-	
					-
Output Capacitance	C _{obo}	-	1.7	4.5	pF
(V _{CB} = 10 V, I _C = 0, f = 1.0 MHz)					
Input Capacitance	C _{ibo}	_	10	-	pF
$(V_{EB} = 0.5 \text{ V}, I_{C} = 0, f = 1.0 \text{ MHz})$	Olpo		10	_	P
$(v_{EB} - 0.0 v, 0.0 - 0, 1 - 1.0 with z)$					
Small – Signal Current Gain	h _{fe}				-
$(I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ kHz})$ BC546		125	_	500	1
BC547/548		125	_	900	1
BC547A		125	220	260	1
BC546B/547B/548B		240	330	500	1
BC547C/548C		450	600	900	
Noise Figure (I _C = 0.2 mA, V _{CE} = 5.0 V, R _S = 2 k Ω , f = 1.0 kHz, Δ f = 200 Hz)	NF				dB
BC546		_	2.0	10	
		_			1
		-	2.0	10	1
BC547 BC548		_	2.0	10	

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

1. I_B is value for which $I_C = 11$ mA at $V_{CE} = 1.0$ V.







BC546B, BC547A, B, C, BC548B, C

ORDERING INFORMATION

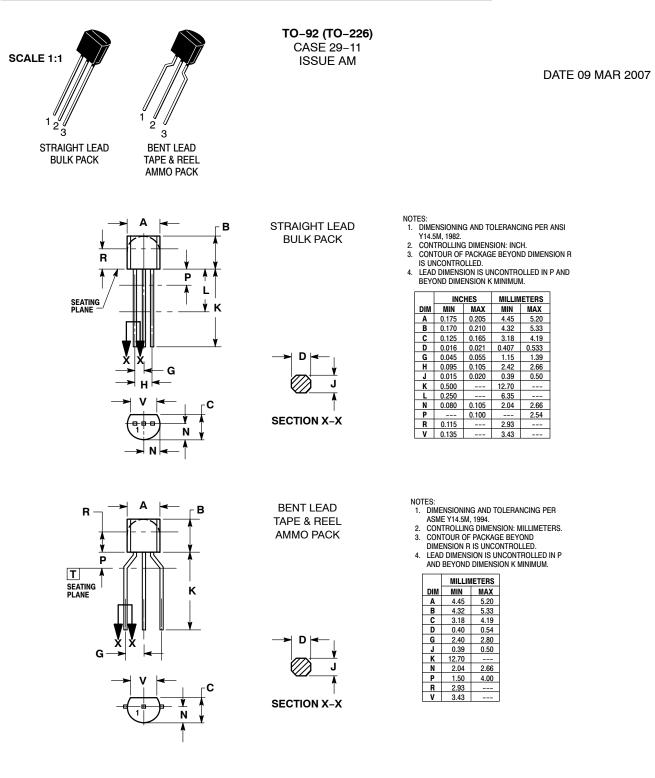
Device	Package	Shipping [†]
BC546B	TO-92	5000 Units / Bulk
BC546BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC546BRL1	TO-92	2000 / Tape & Reel
BC546BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC546BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC547ARL	TO-92	2000 / Tape & Reel
BC547ARLG	TO-92 (Pb-Free)	2000 / Tape & Reel
BC547AZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC547BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC547BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC547BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC547CG	TO-92 (Pb-Free)	5000 Units / Bulk
BC547CZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC548BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC548BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC548BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC548CG	TO-92 (Pb-Free)	5000 Units / Bulk
BC548CZL1G	TO-92 (Pb-Free)	2000 / Ammo Box

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

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STYLES ON PAGE 2

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DATE 09 MAR 2007

STYLE 1: PIN 1. EMITTER 2. BASE 3. COLLECTOR STYLE 6: PIN 1. GATE 2. SOURCE & SUBSTRATE 3. DRAIN STYLE 11: PIN 1. ANODE 2. CATHODE & ANODE 3. CATHODE STYLE 16: PIN 1. ANODE 2. GATE 3. CATHODE STYLE 21: PIN 1. COLLECTOR 2. EMITTER 3. BASE STYLE 22: PIN 1. VCC 2. GROUND 2 3. OUTPUT STYLE 31: PIN 1. GATE 2. DRAIN 3. SOURCE

	BASE EMITTER COLLECTOR
2.	SOURCE DRAIN GATE
2.	MAIN TERMINAL 1 Gate Main Terminal 2
2.	COLLECTOR BASE EMITTER
2.	SOURCE GATE DRAIN

2	1.	ANODE ANODE CATHODE
2	1. 2.	DRAIN Gate Source & Substrate
2	1. 2.	ANODE 1 GATE CATHODE 2
2	1. 2.	ANODE CATHODE NOT CONNECTED
2	1. 2.	GATE SOURCE DRAIN
2	1. 2.	CATHODE ANODE GATE

STYLE 33: PIN 1. RETURN 2. INPUT 3. OUTPUT

2.	CATHODE CATHODE ANODE
2.	BASE 1 EMITTER BASE 2
2.	EMITTER COLLECTOR BASE
	GATE ANODE CATHODE
2.	EMITTER Collector/Anode Cathode
2.	NOT CONNECTED ANODE CATHODE
2.	INPUT GROUND LOGIC

STYLE 4:

STYLE 5: PIN 1. DRAIN 2. SOURCE 3. GATE STYLE 10: PIN 1. CATHODE 2. GATE 3. ANODE STYLE 15: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 STYLE 20: PIN 1. NOT CONNECTED 2. CATHODE 3. ANODE STYLE 25: PIN 1. MT 1 2. GATE 3. MT 2 STYLE 30: PIN 1. DRAIN 2. GATE 3. SOURCE STYLE 35: PIN 1. DRAIN 2. GATE 3. SOURCE STYLE 35: PIN 1. GATE 2. COLLECTOR 3. EMITTER

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